Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims

1. (Currently amended): A method for forming a silicide conductive structure on a semiconductor device, the method comprising:

depositing metal on the surface of a patterned semiconductor film;

heat treating the semiconductor film on which the metal is deposited;

removing residual metal that did not react during the heat treating step; and

repeating a sequence of the depositing step, the heat treating step, and the removing step once or a number of times.

2. (Original): The method for manufacturing the semiconductor device according to claim 1, further comprising:

heat treating the semiconductor film after the repeating step at a temperature that is higher than that of the heat treating step.

3. (Original): The method for manufacturing the semiconductor device according to claim 2, wherein the patterned semiconductor film is an N-type semiconductor.

4. (Currently amended): A method for manufacturing a semiconductor device, comprising:

forming a conductive portion on the substrate, wherein the conductive portion includes a gate electrode;

forming a spacer on a side wall of the gate electrode;

depositing metal on the surface of the substrate including the conductive portion;

applying silicide on the conductive portion in a self-aligned manner by heat treating the substrate on which the metal is deposited;

removing residual metal that did not react during the heat treatment; and

repeating a sequence of the depositing step, the silicide applying step, and the removing step once or a number of times.

5. (Original): The method for manufacturing the semiconductor device according to claim 4, further comprising:

heat treating the substrate after the repeating step at a temperature that is higher than that of the heat treating step.

6. (Original): The method for manufacturing the semiconductor device according to claim 5, wherein the conductive portion to which silicide is applied is an N-type semiconductor.

7. (Original): The method for manufacturing the semiconductor device according to claim 4, wherein the thickness of the gate electrode is 1,000Å (10^{-8}cm) to 2,500Å (10^{-8}crn), and the heat treating is repeated in a temperature range of 600°C to 720°C.

8. (Original): The method for manufacturing the semiconductor device according to claim 7, further comprising:

heat treating the substrate after the repeating step for 30 seconds at a temperature of about 850°C.

9. (Original): The method for manufacturing the semiconductor device according to claim 8, wherein the conductive portion to which silicide is applied is an N-type semiconductor.